

III B. Tech II Semester Supplementary Examinations, November - 2019
VLSI DESIGN

(Common to Electronics and Communication Engineering, Electronics
and Computer Engineering)

Time: 3 hours

Max. Marks: 70

- Note: 1. Question Paper consists of two parts (**Part-A** and **Part-B**)
 2. Answer **ALL** the question in **Part-A**
 3. Answer any **FOUR** Questions from **Part-B**
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PART -A**(14 Marks)**

1.
 - a) Why is VLSI design process presented in NMOS only? Justify with an example. [2M]
 - b) Give the different scaling models and scaling factors. [2M]
 - c) Explain about Inverter Delays. [2M]
 - d) Explain about chip output circuit. [3M]
 - e) What information from the targeted FPGA device is required in RTL synthesis? [3M]
 - f) Explain about Clock Design. [2M]

PART -B**(56 Marks)**

2.
 - a) Derive an equation for I_{ds} of an n-channel Enhancement MOSFET operating in Saturation region. [7M]
 - b) An nMOS transistor is operating in saturation region with the following parameters. $V_{GS} = 5V$; $V_{tn} = 1.2V$; $W/L = 110$; $\mu_n C_{ox} = 110 \mu A/V^2$. Find transconductance of the device. [7M]
3.
 - a) Explain about double poly CMOS rules. [7M]
 - b) Design a layout diagram for CMOS 3-input NAND gate. [7M]
4.
 - a) What is meant by sheet resistance R_s ? Explain the concept of R_s applied to MOS transistors. [7M]
 - b) Calculate on resistance of an inverter from VDD to GND. If n- channel sheet resistance $R_{sn}=104 \Omega$ per square and P-channel sheet resistance $R_{sp} = 3.5 \times 10^4 \Omega$ per square. ($Z_{pu}=4:4$ and $Z_{pd}=2:2$). [7M]
5. Discuss in detail about Fault types and Models. [14M]
6.
 - a) Write down the step by step approach of FPGA design process on XILINX environment. [7M]
 - b) Design a queue and write the dataflow style VHDL program for the same. [7M]
7. Discuss in detail about Low Power CMOS Logic Circuits. [14M]
